

## REMARKS

An Office Action was mailed February 6, 2009. This Response is timely. Any fee due with this paper, including any necessary extension fees, may be charged on Deposit Account 50-1290.

An interview was conducted on May 29. Agreement on the claims was not reached. Nonetheless, the Examiner is thanked for courtesies and considerations extended.

### Summary

Claims 1-3, 5, and 11-18 are being examined. Claim 1 is the only independent claim.

By the foregoing, claim 1 is amended, claim 16 is cancelled, and new claims 19-26 including new independent claims 19 and 26, are presented. No new matter has been added. All new claims are directed to subject matter being examined in the application.

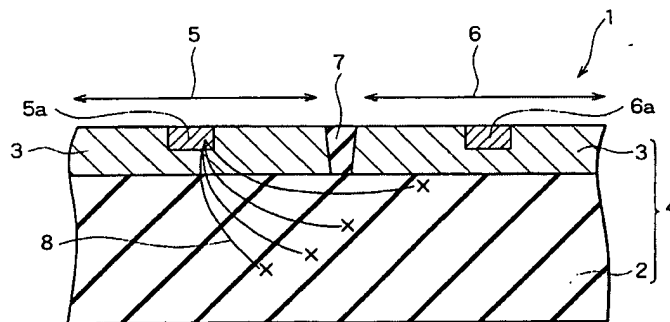
### Rejections in view of Williams

Claims 1, 5, 11-13, 16, and 18 stand rejected under 35 U.S.C. §102(b) as being anticipated by or stand rejected under 35 U.S.C. §103(a) as being unpatentable over U.S. Patent No. 5,156,989 to Williams.

Claims 1 and 19 recite

*[a] device isolation region is spaced apart from the first and second circuit by respective portions of the silicon epitaxial layer.*

Support thereof may be found, inter alia, at 10:27 and Fig. 3.





Thus, the electric signal is not affected by the stray electron since it is not suitably transmitted at the interface. However, a low frequency noise, for example, a switching noise, is transmitted at the interface using the interface state.

When the first and second circuits contact the device isolation region, the first and second circuits are in contact with the interface between the silicon epitaxial layer and the device isolation region. This causes the transmission of the noise between the first and second circuits via the interface.

Therefore, in the presently claimed invention, by spacing the device isolation region apart from the first and second circuits, the integrated circuit can effectively suppress the transmission of the noise. This unexpected result is not taught, disclosed, or suggested in the cited references.

Thus, the claimed structure is not taught by Williams. Accordingly, the Examiner is respectfully requested to withdraw the rejection.

**Rejections in view of Crichi**

Claims 1, 12, and 13 stand rejected under 35 U.S.C. §102(b) as being unpatentable over U.S. Patent No. 5,559,349 to Crichi. Claim 15 stands rejected under 35 U.S.C. §103(a) as being unpatentable over Crichi.

Independent claims 1 and 19 recite

*[a] device isolation region is spaced apart from the first and second circuit by respective portions of the epitaxial layer.*



Thus, claim 14 recites a unique impurity density. This impurity density is in inverse proportion to the resistivity. As taught by the Applicant in Fig. 4, in the presently claimed invention the substrate resistivity dramatically decreases the noise transmission when changing 10 Ohm-cm to 1000 Ohm-cm of the substrate resistivity. Thus, as taught in 13:7-17, by inhibiting the noise transmission to a practically sufficient level, the numerical limitation recited in claim 14 of the present application is achieved.

The combination of William or Crichi, or each of these references alone, teach, disclose, or suggest this inventive structure. Accordingly, the Examiner is respectfully requested to withdraw the rejection.

In view of the remarks set forth above, this application is in condition for allowance which action is respectfully requested. However, if for any reason the Examiner should consider this application not to be in condition for allowance, the Examiner is respectfully requested to telephone the undersigned attorney at the number listed below prior to issuing a further Action.

Respectfully submitted,

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CUSTOMER NUMBER 026304  
Docket No.: NECF 20.702 (100806-00237)